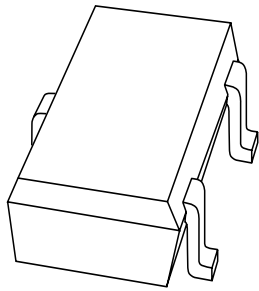


DATA SHEET



2PB1219A

PNP general purpose transistor

Product data sheet
Supersedes data of 1997 Mar 25

1999 Apr 12

PNP general purpose transistor

2PB1219A

FEATURES

- High current (max. 500 mA)
- Low voltage (max. 50 V)
- Low collector-emitter saturation voltage (max. 600 mV).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT323; SC70 plastic package.
NPN complement: 2PD1820A.

MARKING

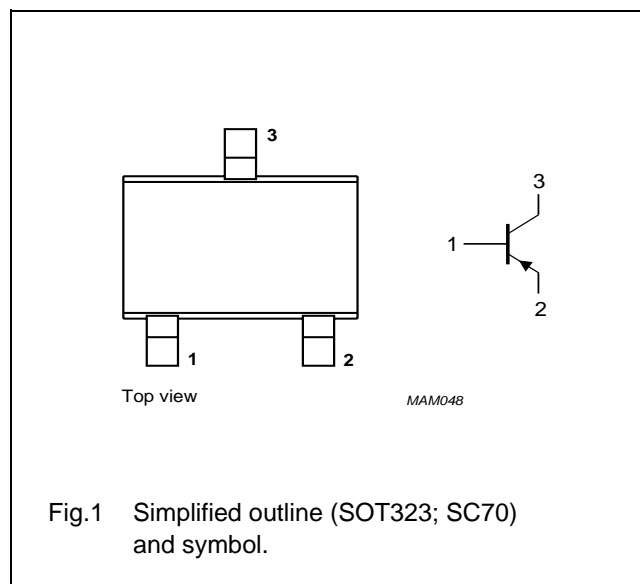
TYPE NUMBER	MARKING CODE ⁽¹⁾
2PB1219AQ	D*Q
2PB1219AR	D*R
2PB1219AS	D*S

Note

- * = - : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–60	V
V_{CEO}	collector-emitter voltage	open base	–	–50	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–500	mA
I_{CM}	peak collector current		–	–1	A
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Refer to SOT323; SC70 standard mounting conditions.

PNP general purpose transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Refer to SOT323; SC70 standard mounting conditions.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = -20\text{ V}$	–	–100	nA
		$I_E = 0$; $V_{CB} = -20\text{ V}$; $T_j = 150\text{ °C}$	–	–5	μA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = -4\text{ V}$	–	–100	nA
h_{FE}	DC current gain	$I_C = -150\text{ mA}$; $V_{CE} = -10\text{ V}$; note 1			
	2PB1219AQ		85	170	
	2PB1219AR		120	240	
	2PB1219AS		170	340	
h_{FE}	DC current gain	$I_C = -500\text{ mA}$; $V_{CE} = -10\text{ V}$; note 1	40	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -300\text{ mA}$; $I_B = -30\text{ mA}$; note 1	–	–600	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -300\text{ mA}$; $I_B = -30\text{ mA}$; note 1	–	–1.5	V
C_c	collector capacitance	$I_E = I_C = 0$; $V_{CB} = -10\text{ V}$; $f = 1\text{ MHz}$	–	15	pF
f_T	transition frequency	$I_C = 50\text{ mA}$; $V_{CE} = -10\text{ V}$; $f = 100\text{ MHz}$; note 1			
	2PB1219AQ		100	–	MHz
	2PB1219AR		120	–	MHz
	2PB1219AS		140	–	MHz

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

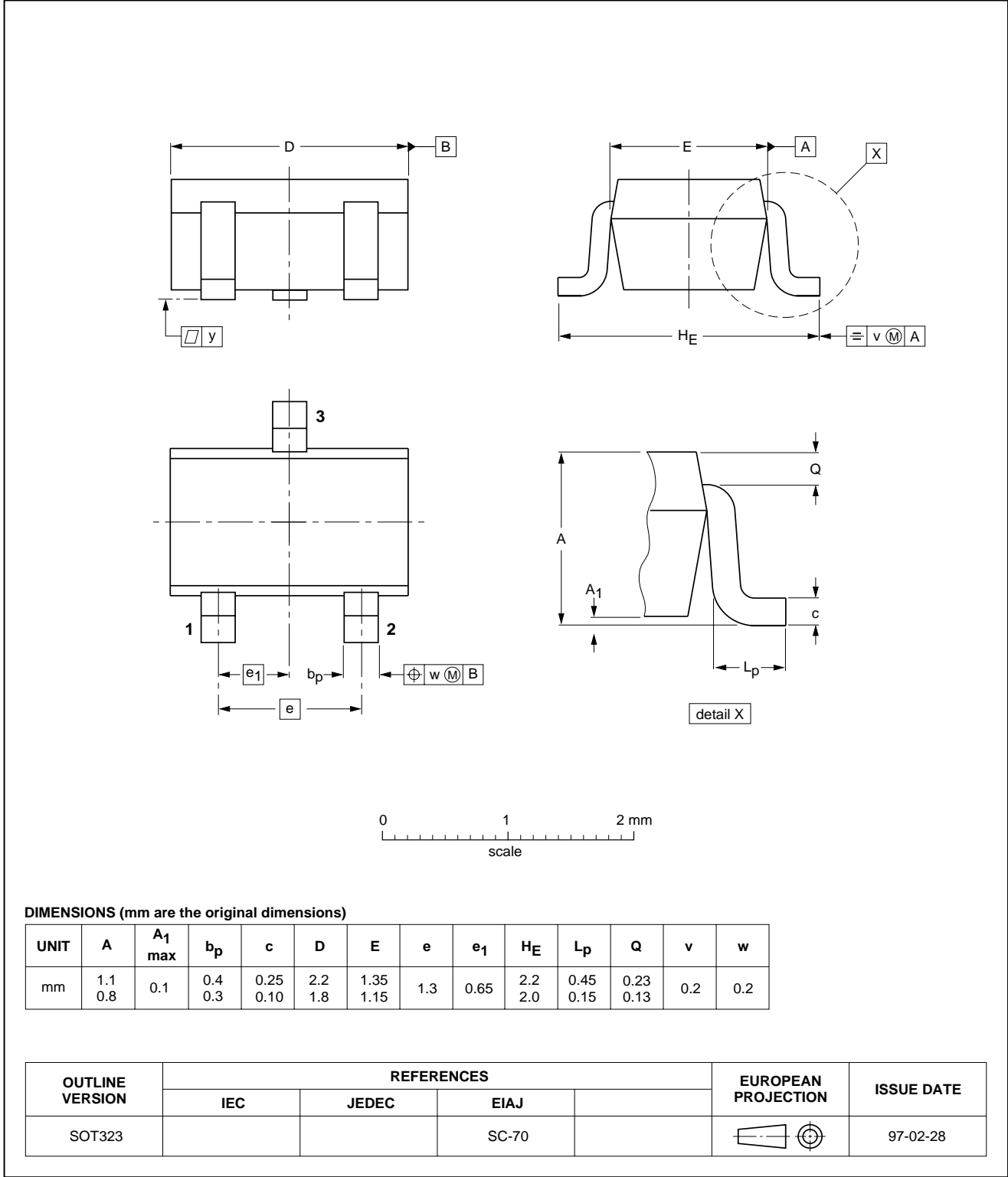
PNP general purpose transistor

2PB1219A

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



PNP general purpose transistor

2PB1219A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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